PC8110xNSZ0F **Series**

DIP 4pin High Speed under High Load Resistance Photocoupler



Description

PC8110xNSZ0F Series contains an IRED optically coupled to a phototransistor built-in schottky barrier diode.

It is packaged in a 4-pin DIP, and SMT gullwing lead-form option.

Input-output isolation voltage(rms) is 5.0kV. CTR is 50% to 400% at input current of 5mA.

Features

- 1. 4pin DIP package
- 2. Double transfer mold package (Ideal for Flow Soldering)
- 3. High speed response at turn-off time due to built-in schottky barrier diode (at saturation mode)
- 4. High isolation voltage between input and output $(V_{iso(rms)}: 5kV)$
- 5. Lead-free and RoHS directive compliant

Agency approvals/Compliance

- 1. Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. PC8110)
- 2. Package resin : UL flammability grade (94V-0)

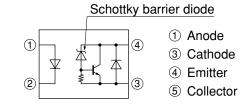
Applications

1. Home appliances

In the absence of confirmation by device specification sheets, SHARP takes no responsibility for any defects that may occur in equipment using any SHARP devices shown in catalogs, data books, etc. Contact SHARP in order to obtain the latest device specification sheets before using any SHARP device.

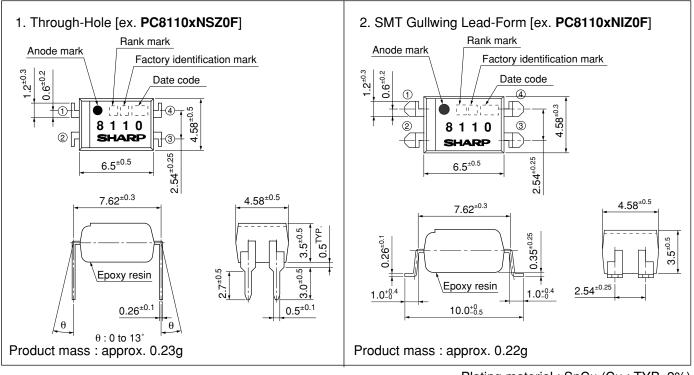


Internal Connection Diagram



Outline Dimensions

(Unit : mm)



Plating material : SnCu (Cu : TYP. 2%)



Date code (2 digit)

1st o	ligit		2nd digit					
Year of p	roduction		Month of production					
Mark	A.D	Mark	Month	Mark				
А	2002	Р	January	1				
В	2003	R	February	2				
С	2004	S	March	3				
D	2005	Т	April	4				
Е	2006	U	May	5				
F	2007	V	June	6				
Н	2008	W	July	7				
J	2009	Х	August	8				
K	2010	А	September	9				
L	2011	В	October	0				
М	2012	С	November	N				
Ν	:	:	December	D				
	Year of p Mark A B C D E F H J K J K L M	A 2002 B 2003 C 2004 D 2005 E 2006 F 2007 H 2008 J 2009 K 2010 L 2011 M 2012	Year of production Mark A.D Mark A 2002 P B 2003 R C 2004 S D 2005 T E 2006 U F 2007 V H 2008 W J 2009 X K 2010 A L 2011 B M 2012 C	Year of productionMonth ofMarkA.DMarkMonthA2002PJanuaryB2003RFebruaryC2004SMarchD2005TAprilE2006UMayF2007VJuneH2008WJulyJ2009XAugustK2010ASeptemberL2011BOctoberM2012CNovember				

repeats in a 20 year cycle

Factory identification mark

Factory identification Mark	Country of origin	
no mark	T	
	Japan	
	Indonesia	
	China	

* This factory marking is for identification purpose only. Please contact the local SHARP sales representative to see the actural status of the production.

Rank mark

Refer to the Model Line-up table

■ Absolute Maximum Ratings

■ Absolute Maximum Ratings (T _a =25°C)								
	Parameter	Symbol	Rating	Unit				
	Forward current	$I_{\rm F}$	50	mA				
Input	*1 Peak forward current	I _{FM}	1.0	Α				
Inj	Reverse voltage	V _R	6	V				
	Power dissipation	Р	70	mW				
	Collector-emitter voltage	V _{CEO}	70	V				
Output	Emitter-collector voltage	V _{ECO}	0.1	V				
Out	Collector current	I _C	30	mA				
	Collector power dissipation	P _C	150	mW				
	Fotal power dissipation	P _{tot}	200	mW				
*2]	solation voltage	V _{iso (rms)}	5.0	kV				
(Operating temperature	T _{opr}	-30 to +100	°C				
S	Storage temperature	T _{stg}	-55 to +125	°C				
*3 🤆	Soldering temperature	T _{sol}	260	°C				

*1 Pulse width≤100µs, Duty ratio : 0.001 *2 40 to 60%RH, AC for 1 minute, f=60Hz

*3 For 10s

■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

								$(1_a = 25 \text{ C})$	
		Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	Forward voltage		$V_{\rm F}$	I _F =20mA	-	1.2	1.4	V	
Input	F	Peak forward voltage		V _{FM}	I _{FM} =0.5A	-	_	3.0	V
	F	Reverse Current		I _R	V _R =4V	-	-	10	μΑ
	Terminal capacitance		Ct	V=0, f=1kHz	-	30	250	pF	
0	(Collector dar	k current	I _{CEO}	$V_{CE}=50V, I_{F}=0$	-	_	100	nA
Output	*4 Collector-emitter breakdown voltage		BV _{CEO}	$I_{C}=0.1 \text{mA}, I_{F}=0$	70	_	-	V	
	0	Collector current		I _C	$I_F=5mA, V_{CE}=5V$	2.5	-	20	mA
	C	Collector-emitter saturation voltage		V _{CE (sat)}	$I_F=20mA$, $I_C=1mA$	-	0.15	0.35	V
	Ι	Isolation resistance		R _{ISO}	DC500V, 40 to 60%RH	5×10 ¹⁰	1011	-	Ω
	F	Floating capacitance		C _f	V=0, f=1MHz	-	0.6	1.0	pF
			Rise time	t _r	$V_{CE}=2V, I_{C}=2mA, R_{L}=100\Omega$	-	3	20	
Transfer		Not saturated	Fall time	$t_{\rm f}$		-	2	10	
charac- teristics	time	Saturated 1	Turn-on time	t _{on}	V_{CC} =5V, I_C =20mA, R_L =10k Ω	-	2	13	
tensues	se ti		Storage time	ts		-	9	50	
	Response		Turn-off time	$t_{\rm off}$		-	23	90	μs
	Res	Saturated 2	Turn-on time	t _{on}	V_{CC} =5V, I_C =20mA, R_L =100k Ω	-	3	13	
			Storage time	ts		-	10	50	
			Turn-off time	t _{off}		-	27	100	

*4 The collector-emitter voltage has negative resistance characteristics since this device has built-in base-emitter resistor.

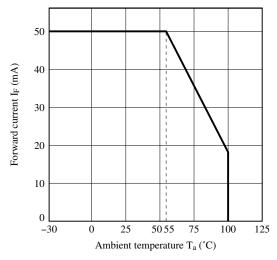
Therefore, please be careful not to provide the voltage that goes beyond absolute maximum ratings.

■ Model Line-up

Lead Form	Through-Hole	SMT G	ullwing	Rank mark	I _C [mA]
Package	100pcs/sleeve	100pcs/sleeve	2000pcs/reel		$(I_F=5mA, V_{CE}=5V, T_a=25^{\circ}C)$
	PC81100NSZ0F	PC81100NIZ0F	PC81100NIP0F	with or without	2.5 to 20.0
	PC81101NSZ0F	PC81101NIZ0F	PC81101NIP0F	А	3.0 to 6.0
	PC81102NSZ0F	PC81102NIZ0F	PC81102NIP0F	В	5.0 to 10.0
Model No.	PC81103NSZ0F	PC81103NIZ0F	PC81103NIP0F	С	7.5 to 15.0
	PC81105NSZ0F	PC81105NIZ0F	PC81105NIP0F	A or B	3.0 to 10.0
	PC81106NSZ0F	PC81106NIZ0F	PC81106NIP0F	B or C	5.0 to 15.0
	PC81108NSZ0F	PC81108NIZ0F	PC81108NIP0F	A, B or C	3.0 to 15.0

Please contact a local SHARP sales representative to inquire about production status.

Fig.1 Forward Current vs. Ambient Temperature





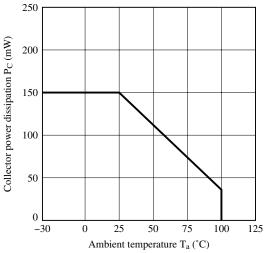


Fig.5 Peak Forward Current vs. Duty Ratio

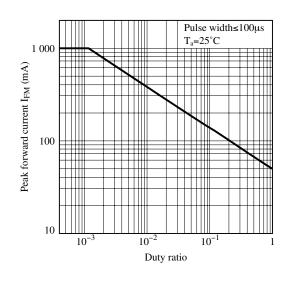


Fig.2 Diode Power Dissipation vs. Ambient Temperature

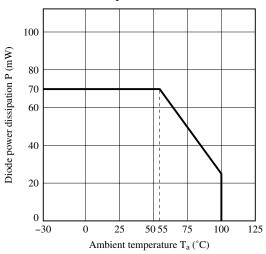


Fig.4 Total Power Dissipation vs. Ambient Temperature

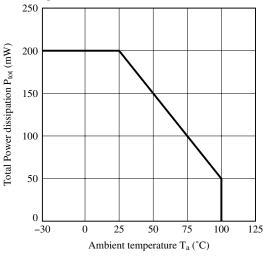


Fig.6 Forward Current vs. Forward Voltage

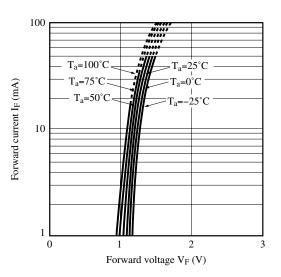
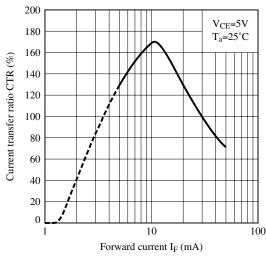
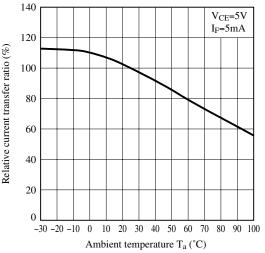




Fig.7 Current Transfer Ratio vs. Forward Current









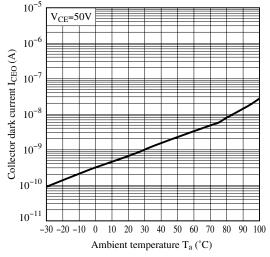


Fig.8 Collector Current vs. Collector-emitter Voltage

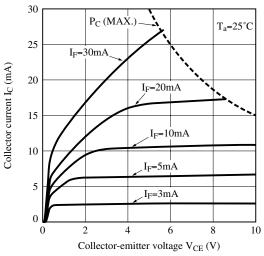
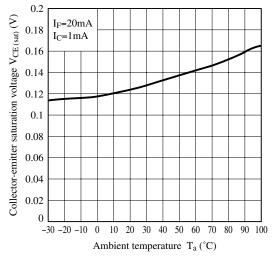
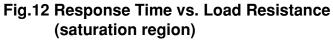


Fig.10 Collector - emitter Saturation Voltage vs. Ambient Temperature





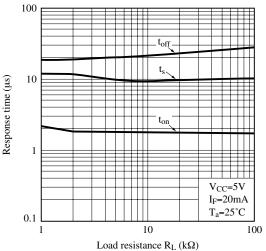




Fig.13 Response Time vs. Load Resistance (active region)

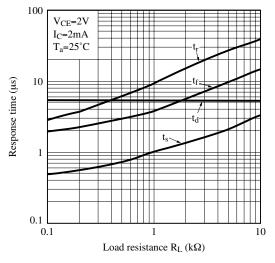


Fig.15 Frequency Response

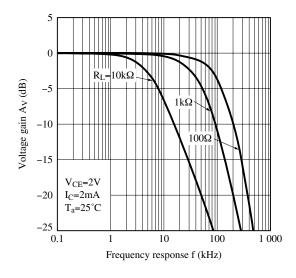
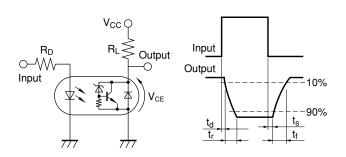
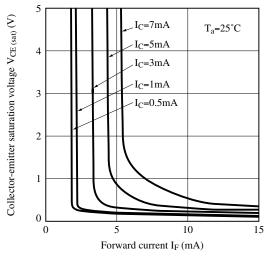


Fig.14 Test Circuit for Response Time



Please refer to the conditions in Fig.12 and Fig.13

Fig.16 Collector-emitter Saturation Voltage vs. Forward Current



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.



Design Considerations

Design guide

While operating at I_F <5.0mA, CTR variation may increase. Please make design considering this fact.

This product is not designed against irradiation and incorporates non-coherent IRED.

The collector-emitter voltage has negative resistance characteristics since this device has built-in base-emitter resistor.

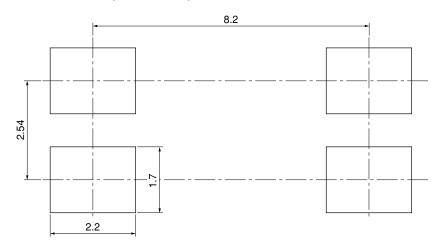
Therefore, please be careful not to provide the voltage that goes beyond absolute maximum ratings.

Degradation

In general, the emission of the IRED used in photocouplers will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

• Recommended Foot Print (reference)



(Unit : mm)

☆ For additional design assistance, please review our corresponding Optoelectronic Application Notes.

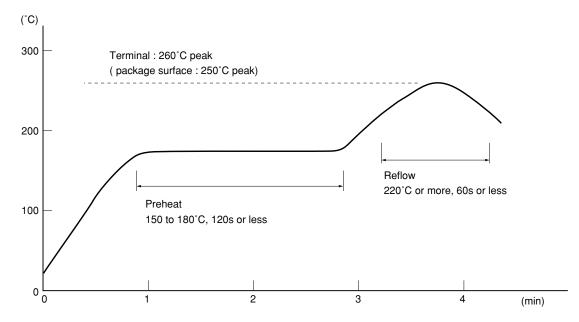


Manufacturing Guidelines

Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below. Soldering should not exceed the curve of temperature profile and time. Please don't solder more than twice.



Flow Soldering :

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 270°C and within 10s. Preheating is within the bounds of 100 to 150°C and 30 to 80s. Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C. Please don't solder more than twice.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



• Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below Immersion time should be 3 minutes or less

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

Presence of ODC

This product shall not contain the following materials. And they are not used in the production process for this product. Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).
•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).



Package specification

Sleeve package

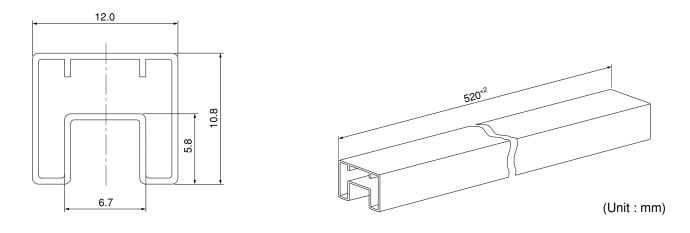
Package materials Sleeve : HIPS (with anti-static material) Stopper : Styrene-Elastomer

Package method

MAX. 100pcs of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

The product shall be arranged in the sleeve with its anode mark on the tabless stopper side. MAX. 20 sleeves in one case.

Sleeve outline dimensions

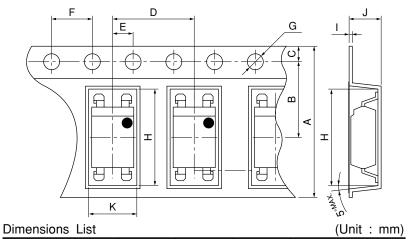




• Tape and Reel package

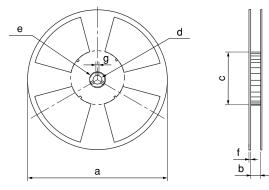
Package materials Carrier tape : PS Cover tape : PET (three layer system) Reel : PS

Carrier tape structure and Dimensions



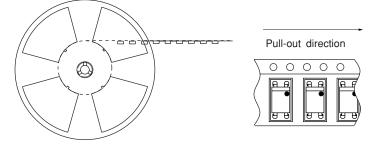
А	В	С	D	Е	F	G
16.0 ^{±0.3}	$7.5^{\pm 0.1}$	$1.75^{\pm 0.1}$	$8.0^{\pm 0.1}$	$2.0^{\pm 0.1}$	$4.0^{\pm 0.1}$	φ1.5 ^{+0.1}
Н	Ι	J	K			
$10.4^{\pm 0.1}$	$0.4^{\pm 0.05}$	$4.2^{\pm 0.1}$	$5.1^{\pm 0.1}$			

Reel structure and Dimensions



_	Dimensio	ns List	(Unit : mm)			
	а	b	с	d		
	330	$17.5^{\pm 1.5}$	100 ^{±1.0}	13 ^{±0.5}		
	e	f	g			
	$23^{\pm 1.0}$	$2.0^{\pm 0.5}$	$2.0^{\pm 0.5}$			

Direction of product insertion



[Packing : 2 000pcs/reel]

SHARP

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- --- Personal computers
- --- Office automation equipment
- --- Telecommunication equipment [terminal]
- --- Test and measurement equipment
- --- Industrial control
- --- Audio visual equipment
- --- Consumer electronics

(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection with equipment that requires higher reliability such as:

- --- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- --- Traffic signals
- --- Gas leakage sensor breakers
- --- Alarm equipment
- --- Various safety devices, etc.

(iii) SHARP devices shall not be used for or in connection with equipment that requires an extremely high level of reliability and safety such as:

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- --- Telecommunication equipment [trunk lines]
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